ABSTRACT

This application report provides guidelines and recommendations for implementing BUCK1 controller current sense using resistance of the inductor (DCR current-sensing method) for TPS65311-Q1 and TPS65310A-Q1 devices. This method was verified on the TPS65311-Q1 device. However, the BUCK1 controller is identical between TPS65310A-Q1 and TPS65311-Q1 devices and the results should be applicable to TPS65310A-Q1 device also.

1 Introduction

BUCK1 controller in the TPS65310A-Q1 and TPS65311-Q1 devices operate using constant frequency peak current mode control. Peak current-mode control regulates the peak current through the inductor such that the output voltage VBUCK1 is maintained to its set value. The error between the feedback voltage VSENSE1 and the internal reference produces an error signal at the output of the error amplifier (COMP1), which serves as target for the peak inductor current. At S1–S2, the current through the inductor is sensed as a differential voltage and compared with this target during each cycle. For applications which require precise current sensing, typically an external shunt resistor is used. But, the external sense resistor could be bulky and also for better efficiency, the resistance of the inductor (DCR) can be used to sense the inductor current. Figure 1 shows the typical block diagram for both current sensing methods.
2 Sense Resistor Method

As specified in the TPS65311-Q1 datasheet (section: Output Inductor, Sense Resistor and Capacitor Selection for the BUCK1 Controller), an external resistor-\( R_s \), is used to sense the current through the inductor. The current sense resistor pins, S1 and S2, are fed into an internal differential amplifier which supports the range of VBUCK1 voltages. The sense resistor, \( R_s \), must be chosen so that the maximum forward peak current in the inductor generates a voltage of 75 mV across the sense pins. This specified typical value is for low duty cycles only. At typical duty-cycle conditions around 28% (assuming 3.3-V output and 12-V input), 50 mV is a more reasonable value, considering tolerances and mismatches. Use Figure 2 (Reduction of Current-Limit vs Duty Cycle) of the TPS65311-Q1 datasheet to estimate the maximum sense voltage across the sense resistor for different duty cycles.

\[
R_s = \frac{50 \, \text{mV}}{I_{\text{max, peak}}}
\]  

(1)

Optimal slope compensation which is adaptive to changes in input voltage and duty cycle allows stable operation at all conditions. For the optimal performance of the slope compensation circuit, empirical Equation 2 must be followed while choosing the inductor and the sense resistor.

\[
L = 410 \times R_s
\]

where
- \( L \) = inductor in \( \mu \text{H} \)
- \( R_s \) = external sense resistor in \( \Omega \)

3 DCR Sensing Method

The current sense pins, S1 and S2, are high-impedance pins with low leakage across the VBUCK1 operating range. This allows current sensing using the DC resistance, \( R_L \) or DCR of the inductor, for better efficiency and this eliminates the need of additional sense resistor to save cost and PCB space. For DCR sensing method, a RC network, \( R_{\text{DCR}} \) and \( C_{\text{DCR}} \), is used in parallel to the inductor. The voltage across \( C_{\text{DCR}} \) will be directly proportional to the inductor current \( (I_L) \), as expressed in Equation 3 and Equation 4.

\[
R_{\text{DCR}} \times C_{\text{DCR}} = \frac{L}{R_L}
\]

(3)

\[
V_{\text{DCR}} = I_L \times R_L
\]

(4)

where
- \( R_{\text{DCR}}, C_{\text{DCR}} \) = external RC network used in parallel to the inductor
- \( L \) = inductor in \( \mu \text{H} \)
- \( R_L \) = Inductor DC resistance
- \( V_{\text{DCR}} \) = voltage across sense capacitor

A 10-\( \mu \text{H} \) inductor with the specification in Table 1 was used for these measurements.

<table>
<thead>
<tr>
<th>Part Number</th>
<th>Inductance (( \mu \text{H} ))</th>
<th>DCR (m( \Omega ))</th>
<th>SRF Typical (MHz)</th>
<th>Isat (A)</th>
<th>Irms (A)</th>
</tr>
</thead>
<tbody>
<tr>
<td>MSS1260T-103ML</td>
<td>10 ( \pm 20% )</td>
<td>21.5</td>
<td>22</td>
<td>6</td>
<td>3</td>
</tr>
</tbody>
</table>

Table 1. Inductor Specification
Based on Equation 3, with L= 10 µH, R<sub>L</sub> = 21.5 mΩ, and by assuming C<sub>DCR</sub> = 220 nF, the result is:

\[ R_{DCR} = 2.11 \, KΩ \]

For this experiment, R<sub>DCR</sub> = 2 KΩ was used as it was the closest available resistor value when compared with 2.11 KΩ.

Different combinations of C<sub>DCR</sub> and R<sub>DCR</sub> can also work, but this experiment uses C<sub>DCR</sub> = 220 nF.

### 4 Temperature Dependency of Inductor Series Resistance

Inductor series resistance (DCR) is a resistance of copper coil that varies with temperature.

Temperature dependency of inductor series resistance is given in Equation 5:

\[ R_L(T) = R_{L,25°C} \times \left[ 1 + TC_{Copper} \times (T - 25) \right] \]

where

- T= temperature of the inductor
- R<sub>L,25°C</sub> = inductor series resistance at room temperature (25°C)
- TC<sub>Copper</sub> = temperature coefficient of copper that is equal to 0.00393

### 5 Measurement Procedure

Since the resistance of the inductor (DCR) varies with temperature, measurements were taken across temperature to check the effect of temperature on the DCR current-sensing method. BUCK1 overcurrent detection causes device reset and RESN is pulled low. DC load current at which the device detects BUCK1 overcurrent (OC) is noted and recorded as the overcurrent detection threshold. However, actual inductor-peak current will be higher than this average DC current and can be estimated based on the differential voltage measured across the current sense resistor, R<sub>S</sub>, (when using the Sense Resistor Method) or across C<sub>DCR</sub> (when using DCR Sensing Method). Since measuring actual inductor current with a current probe requires the inductor to be lifted off the board, this causes accuracy issues and difficulty in measuring the inductor current across temperature.

The scope of this measurement is to check the basic functionality and feasibility of the DCR Sensing Method for this device. These measurements are not intended for optimization of the DCR Sensing Method circuit, nor a reference design for a production application. Any adaption by customers must be validated in customers’ own design and environment.

#### 5.1 Test Conditions

The test conditions are as follows:

- Device Input Supply voltage, VBAT = 12 V (bench-top power supply with 4-A current rating)
- BUCK1 Output Voltage, VBUCK1 = 3.35 V
- Load current on VBUCK1 = Electronic source meter with 3.1 A maximum DC-load current capability
- Case 1, Sense Resistor Method:
  - Reference measurement using 22-mΩ current-sense resistor
  - TPS65311-Q1 EVM with 22-mΩ current-sense resistor for BUCK1 current sensing
- Case 2, DCR Sensing Method:
  - Measurement using DCR current sense using R<sub>DCR</sub> (2 kΩ), C<sub>DCR</sub> (220 nF), and 10 µH inductor with 21.5 mΩ DCR

TPS65311 EVM was modified by shorting 22-mΩ current-sense resistor and placing R<sub>DCR</sub> (2 kΩ) and C<sub>DCR</sub> (220 nF) across the inductor. Voltage across the sense capacitor was measured using a differential probe. Voltage spikes were observed during the measurements, which could be due to the board modifications that had to be made, such as cutting the trace and blue wiring. However, to demonstrate feasibility, the spikes should be acceptable.
Since the load-current source had a maximum current of 3.1 A, two parallel current-source meters were used in the case where the load current required to detect the overcurrent exceeded 3.1 A (due to limitations of load current source).

Using the DCR Sensing Method, there was a negative offset of approximately 10 mV, which can be adjusted by a slightly different combination of $R_{DCR}$ and $C_{DCR}$ to make the baseline close to 0 mV. This offset could be due to the slight mismatch in the RC time constants according to Equation 4 or due to the blue wiring or measurement setup.

5.2 Measurement Results

All measurement plots taken at room temperature (except Figure 12). The following is the legend for Figure 4 through Figure 12:

- Blue trace: BUCK1 output Voltage
- Green trace: SW1 voltage
- Red trace: Differential voltage measured across sense resistor (Case-1) or Differential voltage measured across $C_{DCR}$ (Case-2)
- Pink trace: Load current on BUCK1

![Figure 2. TPS65311-EVM Top View](image2)

![Figure 3. TPS65311-EVM Bottom View](image3)

![Figure 4. Case 1: Measurement With No Load Condition](image4)

![Figure 5. Case 2: Measurement With No Load Condition](image5)
Device detects OC at around 68 mV

Figure 6. Case 1: Measurement With DC load — 1 A

Figure 7. Case 2: Measurement with DC load — 1 A

Figure 8. Case 1: Measurement With DC load — 2 A

Figure 9. Case 2: Measurement With DC load — 2 A

Just before OC Detection

Figure 10. Case-1: Measurement With DC load — 2.6 A

Figure 11. Case 2: Measurement With 3.2 A (2.70 A and 0.5 A) Load

Device detects OC at around 68 mV

Just before OC detection, 0.5 A load current through 2nd source-meter is not shown
5.3 Estimation of Peak Inductor Current at Which Device Has Detected Overcurrent (OC)

Based on Figure 2 of the TPS65311-Q1 datasheet, for \( V_{in} = 12 \) V and \( V_{out} = 3.3 \) V, the current limit voltage (across S1-S2) of approximately 68 mV is almost the same value as observed in the measurement plots. This estimation is done to validate the measurement results by back calculating the average DC current at which device detected the overcurrent threshold.

5.3.1 Case 1, Sense Resistor Method

Based on Figure 10, inductor peak current is calculated as:

\[
I_{L_{\text{max}}} = \frac{68 \text{ mV}}{22 \text{ m\Omega}} = 3.1 \text{ A}
\]  

(6)

\[
I_{L_{\text{min}}} = \frac{50 \text{ mV}}{22 \text{ m\Omega}} = 2.27 \text{ A}
\]  

(7)

With Inductor min and max currents the DC load current can be back calculated as follows:

\[
I_{DC} = \frac{(I_{L_{\text{max}}} + I_{L_{\text{min}}})}{2} = 2.69 \text{ A}
\]  

(8)
Calculated DC current is very close to the actual DC load current (2.6 A) at which device detected overcurrent threshold. Thus, the calculation correlates and the current is fairly constant across temperature.

### 5.3.2 Case 2, DCR Sensing Method

As shown in Figure 5, there is an approximately –10 mV offset, which must be accounted for while doing back calculation of peak inductor current based on measured sense voltage. Based on Figure 11, the measured peak voltage was 68 mV and 78 mV must be used for peak-inductor current (IL\_max) calculation. Similarly for IL\_min calculation, 56 mV was taken instead of measured value of around 46 mV. (In Figure 11, there is an undershoot due to measurement issue and hence cursor measured value (46mV) was taken for IL\_min calculation.)

\[
\text{IL\_max} = \frac{78 \text{ mV}}{21.5 \text{ m}\Omega} = 3.66 \text{ A} \\
\text{IL\_min} = \frac{56 \text{ mV}}{21.5 \text{ m}\Omega} = 2.64 \text{ A}
\]

(9) (10)

With Inductor min and max currents the DC load current is calculated by:

\[
I_{DC} = \frac{(IL\_max + IL\_min)}{2} = 3.15 \text{ A}
\]

(11)

Considering the tolerances, calculated DC current is close to the actual DC load current (3.2 A) and the calculation looks correlated.

Inductor resistance across temperature can be calculated according to Equation 5 and then used to calculate the peak inductor current at which OC is detected. This will be an approximation as there are additional tolerances due to actual inductor resistance, variation of sense capacitor (C\_DCR) across temperature, measurement accuracy, and other variations.

**Table 3. Calculation of Peak Inductor Current at OC Detection Point for DCR Sensing Method**

<table>
<thead>
<tr>
<th>Ambient Temperature</th>
<th>Case-2, DCR Sensing Method</th>
</tr>
</thead>
<tbody>
<tr>
<td></td>
<td>Inductor Resistance (ohm) (RL) (Calculated Based on Equation 5)</td>
</tr>
<tr>
<td>–40C</td>
<td>0.0160</td>
</tr>
<tr>
<td>–25C</td>
<td>0.0173</td>
</tr>
<tr>
<td>0C</td>
<td>0.0194</td>
</tr>
<tr>
<td>+25C</td>
<td>0.0215</td>
</tr>
<tr>
<td>+50C</td>
<td>0.0236</td>
</tr>
<tr>
<td>+75C</td>
<td>0.0257</td>
</tr>
<tr>
<td>+100C</td>
<td>0.0278</td>
</tr>
<tr>
<td>+125C</td>
<td>0.0299</td>
</tr>
</tbody>
</table>

### 5.3.3 Measurements Summary

Figure 13 provides the measurement plots (based on Table 2 and Table 3) for both methods across temperature. It is evident from the results that the sense resistor method has less variation across temperature and the DCR current sense method has considerable variation across temperature. Also, estimated peak current (assuming that peak current is proportional to average DC current) is correlating with the measured DC current between 0°C to 50°C and beyond this temperature range there is a wider difference between calculated and the measured values.
6 Conclusion

- As expected, DCR Sensing Method has a wide variation across temperature. To accommodate for these variations, an inductor with large current rating and tighter DCR tolerance must be used. Since it needs an additional two components (R_{DCR}, C_{DCR}), accuracy of current sense also depends on accuracy of these two components.

- With DCR current-sensing method, BUCK1 controller efficiency can be improved as it eliminates the drop across the external sense resistor. This method will also help to save PCB space, as sense resistor is usually bulky.

- As DCR current sensing requires an inductor with a larger current rating and better tolerance along with additional two components, it may offset the cost of an additional sense resistor. A cost comparison between these two current sensing methods should be performed to determine the correct level of cost and performance optimization.

- Current sensing with external sense resistor, R_S, is very stable across temperature.

- With DCR Sensing Method, larger inductor-current ripple was observed at high temperature and might affect the EMC performance.

- Electrical and EMC performance of DCR Sensing Method must be studied by the customer in their application to ensure the applicability to use this method in the specific application use case.

Revision History

<table>
<thead>
<tr>
<th>DATE</th>
<th>REVISION</th>
<th>NOTES</th>
</tr>
</thead>
<tbody>
<tr>
<td>September 2016</td>
<td>*</td>
<td>Initial Release</td>
</tr>
</tbody>
</table>
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